

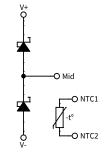
1700 V, 600 A, Silicon Carbide, Half-Bridge Rectifier

$\mathbf{V}_{_{\mathrm{R}}}$	1700 V
I <sub>F</sub>	600 A

#### **Technical Features**

- Ultra-Low Loss, High Frequency Operation
- Low Forward Voltage (V<sub>F</sub>) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Temperature-Independent Switching Behavior





## **Applications**

- Railway, Traction, and Motor Drives
- EV Chargers
- High-Efficiency Converters / Inverters
- Renewable Energy
- Smart-Grid / Grid-Tied Distributed Generation

## **System Benefits**

- Enables Compact, Lightweight Systems
- Increased System Efficiency, due to Low Switching & Conduction Losses of SiC
- Reduced Thermal Requirements and System Cost

## **Maximum Parameters (Verified by Design)**

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions	Note
Maximum Reverse Voltage	$V_{R-Max}$			1700	V		
	I <sub>F</sub>		986			T <sub>C</sub> = 25°C, T <sub>VJ</sub> ≤ 175°C	
Continuous Forward Current			702			T <sub>C</sub> = 90°C, T <sub>VJ</sub> ≤ 175°C	
Maximum Pulsed Forward Current	I <sub>F (Pulsed)</sub>			1200	A	$t_{Pmax}$ limited by $T_{VJmvax}$ $T_C = 25$ °C	
Maximum Virtual Junction Temperature	T <sub>vJ</sub>	-40		175	°C		

# Diode Characteristics (Per Position) ( $T_{VJ} = 25$ °C unless otherwise specified)

Parameter	Symbol	Min.	Тур.	Max.	Unit	<b>Test Conditions</b>	Note
Diada Famuard Valtara	V		1.6		V	I <sub>F</sub> = 600 A	
Diode Forward Voltage	V <sub>F</sub>		2.2			I <sub>F</sub> = 600 A, T <sub>VJ</sub> = 175°C	
Reverse Current			0.06			V <sub>R</sub> = 1700 V, T <sub>VJ</sub> = 25°C	
Reverse Current	I <sub>R</sub>		0.29	0.29 mA	mA	V <sub>R</sub> = 1700 V, T <sub>VJ</sub> = 175°C	
Total Capacitive Charge	Qc		4.9		mC	V <sub>R</sub> = 1100 V	
			55.7		nF	V <sub>R</sub> = 0 V, f = 100 kHz	
Total Capacitance	С		2.9	nl		V <sub>R</sub> = 550 V, f = 100 kHz	
			2.7			V <sub>R</sub> = 1100 V, f = 100 kHz	
Thermal Resistance, Junction to Case	R <sub>TH-JC</sub>		0.048			Per position	

#### Note:

 $<sup>^{1}</sup>$  SiC Schottky diodes are majority carrier devices, so there is no reverse recovery charge.

## **Module Physical Characteristics**

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Package Resistance, M1 (High-Side)	R <sub>1-2</sub>		106.5		0	T <sub>c</sub> = 125°C, Note 1
Package Resistance, M2 (Low-Side)	R <sub>2-3</sub>		126.3		μΩ	T <sub>c</sub> = 125°C, Note 1
Stray Inductance	$L_{Stray}$		4.9		nH	Between DC- and DC+, f = 10 MHz
Case Temperature	T <sub>c</sub>	-40		125	°C	
Manustina Tanana		3	4.5	5	N-m	Baseplate, M6 bolts
Mounting Torque	Ms	0.9	1.1	1.3		Power Terminals, M4 bolts
Weight	W		167		g	
Case Isolation Voltage	V <sub>isol</sub>	4			kV	AC, 50 Hz, 1 minute
Comparative Tracking Index	СТІ	600				
Classica Distance		13.07				Terminal to Terminal
Clearance Distance		6.00				Terminal to Heatsink
6 5		14.27			mm	Terminal to Terminal
Creepage Distance		12.34				Terminal to Heatsink

# NTC Characteristics (T<sub>NTC</sub> = 25 °C unless otherwise specified)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Notes
Resistance at 25°C	R <sub>25</sub>		4700		Ω	
Tolerance of R <sub>25</sub>			±1		%	
Beta Value for 25°C to 85°C	B <sub>25/85</sub>		3435		К	
Beta Value for 0°C to 100°C	B <sub>0/100</sub>		3399		K	
Tolerance of B <sub>25/85</sub>			±1		%	
Maximum Power Dissipation	P <sub>Max</sub>		50		mW	

# Steinhart & Hart Coefficients for NTC Resistance & NTC Temperature Computation (T in K)

$$\ln\left(\frac{R}{R_{25}}\right) = A + \frac{B}{T} + \frac{C}{T^2} + \frac{D}{T^3}$$

$$\ln\left(\frac{R}{R_{25}}\right) = A + \frac{B}{T} + \frac{C}{T^2} + \frac{D}{T^3}$$

$$\frac{1}{T} = A_1 + B_1 \ln\left(\frac{R}{R_{25}}\right) + C_1 \ln^2\left(\frac{R}{R_{25}}\right) + D_1 \ln^3\left(\frac{R}{R_{25}}\right)$$

A <sub>1</sub>	B <sub>1</sub>	C <sub>1</sub>	$D_1$
3.354E-03	3.001E-04	5.085E-06	2.188E-07

## **Typical Performance**

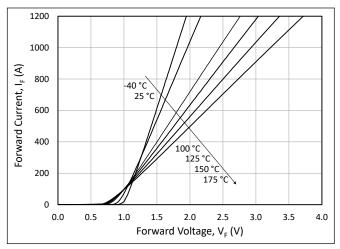


Figure 1. Typical Forward Characteristics

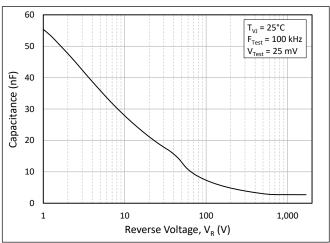
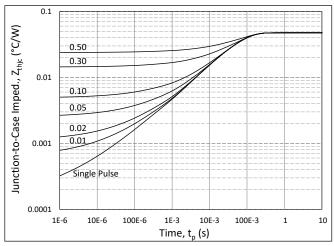


Figure 3. Typical Capacitance vs. Reverse Voltage



**Figure 5.** Diode Junction to Case Transient Thermal Impedance,  $Z_{th JC}$  (°C/W)

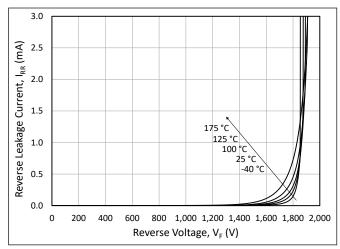


Figure 2. Typical Reverse Characteristics

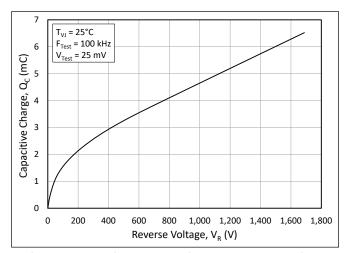


Figure 4. Typical Capacitive Charge vs. Reverse Voltage

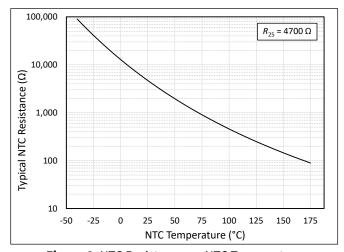
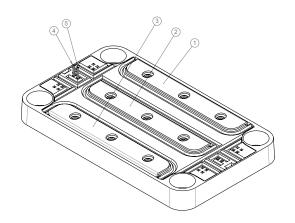
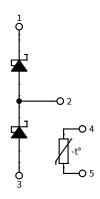


Figure 6. NTC Resistance vs. NTC Temperature

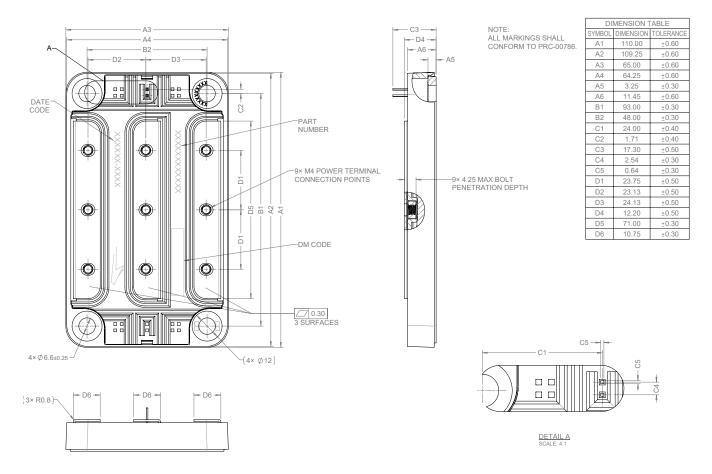
## **Schematic and Pin Out**



PIN OUT SCHEME					
PIN	LABEL				
1	V+				
2	Mid				
3	V-				
4	NTC1				
(5)	NTC2				
(5)					



## **Package Dimension (mm)**



## **Supporting Links & Tools**

### **Evaluation Tools & Support**

- CAR600M17HN6 PLECS Model
- SpeedFit 2.0 Design Simulator™
- Technical Support Forum

### **Application Notes**

- CPWR-AN35: 62mm Thermal Interface Material Application Note
- CPWR-AN39: KIT-CRD-CIL12N-HM User Guide

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#### **Contact info:**

4600 Silicon Drive Durham, NC 27703 USA Tel: +1.919.313.5300 www.wolfspeed.com/power